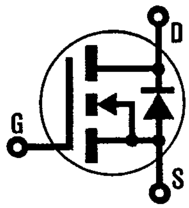
Data Sheet No. PD-9.309G
T-39-11

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS IRF630 IRF631 IRF632 IRF633



N-Channel

TO-220

200 Volt, 0.4 Ohm HEXFET TO-220AB Plastic Package

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

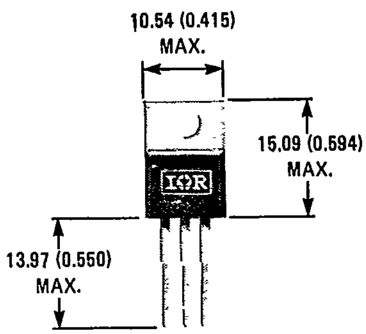
Features:

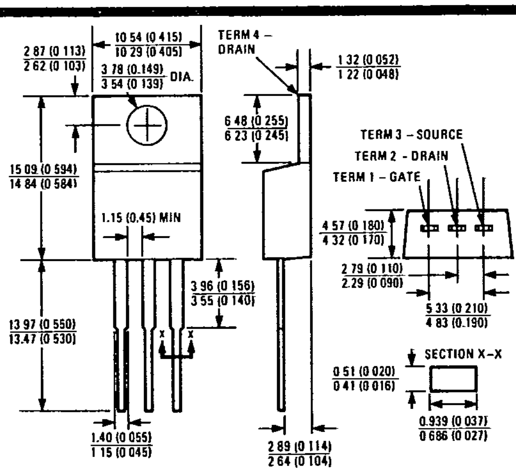
- Compact Plastic Package
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRF630	200V	0.4Ω	9.0A
IRF631	150V	0.4Ω	9.0A
IRF632	200V	0.6Ω	8.0A
IRF633	150V	0.6Ω	8.0A

CASE STYLE AND DIMENSIONS





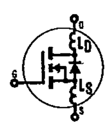
Case Style TO-220AB
Dimensions in Millimeters and (Inches)

IRF630, IRF631, IRF632, IRF633 Devices

Absolute Maximum Ratings

Parameter		IRF630	IRF631	IRF632	IRF633	Units
V_{DS}	Drain - Source Voltage ①	200	150	200	150	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 kΩ) ①	200	150	200	150	V
I_D @ T_C = 25°C	Continuous Drain Current	9.0	9.0	8.0	8.0	A
I_D @ T_C = 100°C	Continuous Drain Current	6.0	6.0	5.0	5.0	A
I_{DM}	Pulsed Drain Current ③	36	36	32	32	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	75 (See Fig. 14)				W
	Linear Derating Factor	0.6 (See Fig. 14)				W/K④
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 36	36	32	32	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	−55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions	
BV_{DSS}	Drain - Source Breakdown Voltage	IRF630 IRF632	200	—	—	V	V_{GS} = 0V	
		IRF631 IRF633	150	—	—	V	I_D = 250μA	
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250μA	
I_{GSS}	Gate-Source Leakage Forward	ALL	—	—	500	nA	V_{GS} = 20V	
I_{GSS}	Gate-Source Leakage Reverse	ALL	—	—	−500	nA	V_{GS} = −20V	
I_{DSS}	Zero Gate Voltage Drain Current	ALL	—	—	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V	
			—	—	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C	
$I_{D(on)}$	On-State Drain Current ②	IRF630 IRF631	9.0	—	—	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)}$ max., V_{GS} = 10V	
		IRF632 IRF633	8.0	—	—	A		
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRF630 IRF631	—	0.25	0.4	Ω	V_{GS} = 10V, I_D = 5.0A	
		IRF632 IRF633	—	0.4	0.6	Ω		
g_{fs}	Forward Transconductance ②	ALL	3.0	4.8	—	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)}$ max., I_D = 5.0A	
C_{iss}	Input Capacitance	ALL	—	600	800	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10	
C_{oss}	Output Capacitance	ALL	—	250	450	pF		
C_{rss}	Reverse Transfer Capacitance	ALL	—	80	150	pF		
$t_{d(on)}$	Turn-On Delay Time	ALL	—	—	30	ns	V_{DD} = 90V, I_D = 5.0A, Z_o = 15Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)	
t_r	Rise Time	ALL	—	—	50	ns		
$t_{d(off)}$	Turn-Off Delay Time	ALL	—	—	50	ns		
t_f	Fall Time	ALL	—	—	40	ns		
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	19	30	nC	V_{GS} = 10V, I_D = 12A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)	
Q_{gs}	Gate-Source Charge	ALL	—	10	—	nC		
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	—	9.0	—	nC		
L_D	Internal Drain Inductance	ALL	—	3.5	—	nH	Measured from the contact screw on tab to center of die.	Modified MOSFET symbol showing the internal device inductances.
			—	4.5	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.	
L_S	Internal Source Inductance	ALL	—	7.5	—	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.	

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	—	—	1.67	K/W ④	
R_{thCS}	Case-to-Sink	ALL	—	1.0	—	K/W ④	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	—	—	80	K/W ④	Typical socket mount

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRF630 IRF631	—	—	9.0	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRF632 IRF633	—	—	8.0	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRF630 IRF631	—	—	36	A	
		IRF632 IRF633	—	—	32	A	
V_{SD}	Diode Forward Voltage ②	IRF630 IRF631	—	—	2.0	V	$T_C = 25°C, I_S = 9.0A, V_{GS} = 0V$
		IRF632 IRF633	—	—	1.8	V	$T_C = 25°C, I_S = 8.0A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	ALL	—	450	—	ns	$T_J = 150°C, I_F = 9.0A, dI_F/dt = 100\ A/\mu s$
Q_{RR}	Reverse Recovered Charge	ALL	—	3.0	—	μC	$T_J = 150°C, I_F = 9.0A, dI_F/dt = 100\ A/\mu s$
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

① $T_J = 25°C$ to $150°C$. ② Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).
④ K/W = °C/W
W/K = W/°C

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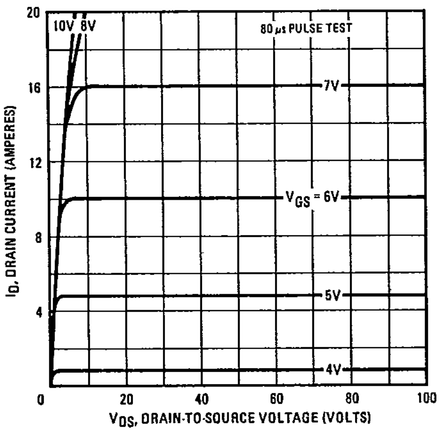

Fig. 1 — Typical Output Characteristics

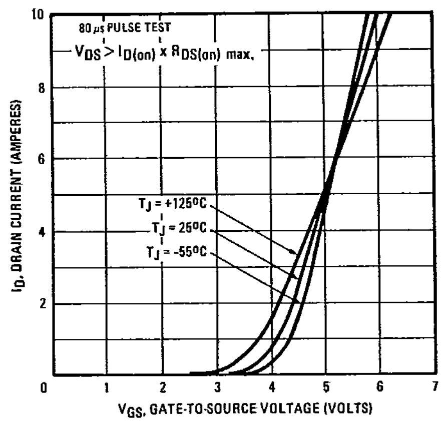

Fig. 2 — Typical Transfer Characteristics

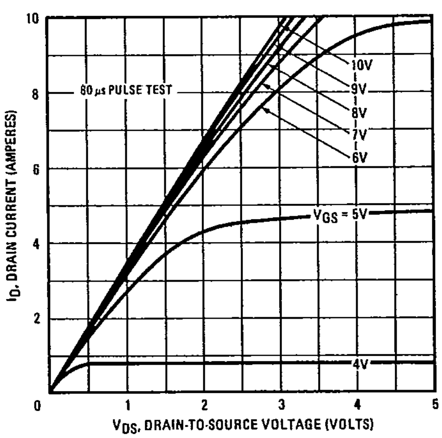

Fig. 3 — Typical Saturation Characteristics

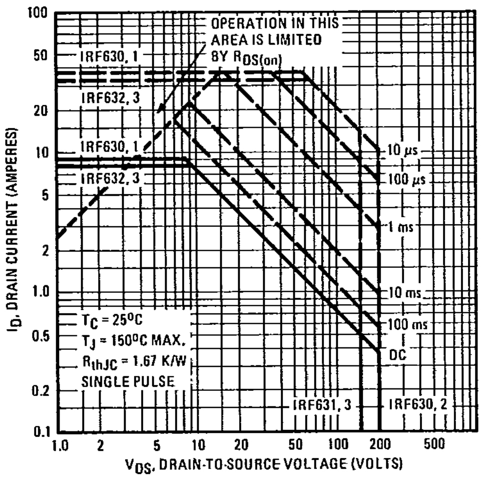

Fig. 4 — Maximum Safe Operating Area

IRF630, IRF631, IRF632, IRF633 Devices

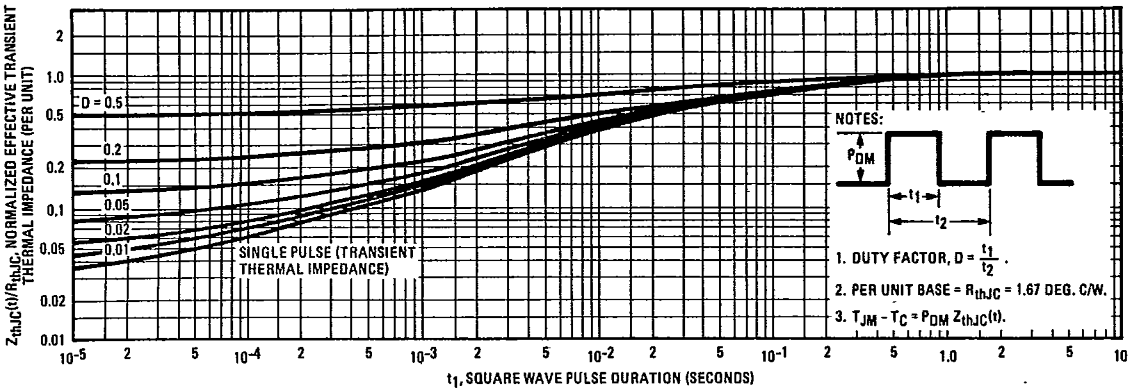

Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

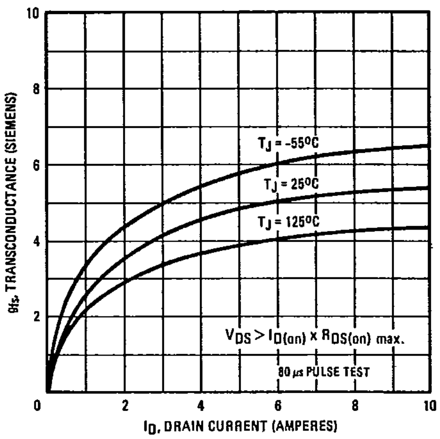

Fig. 6 — Typical Transconductance Vs. Drain Current

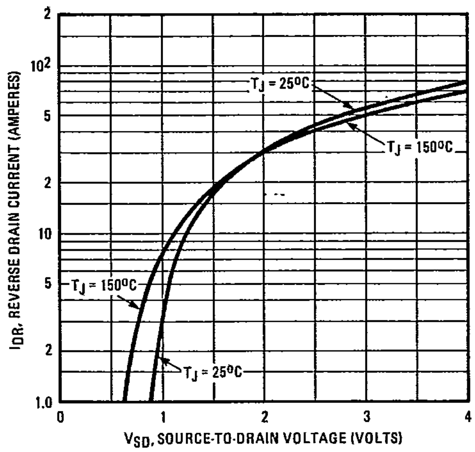

Fig. 7 — Typical Source-Drain Diode Forward Voltage

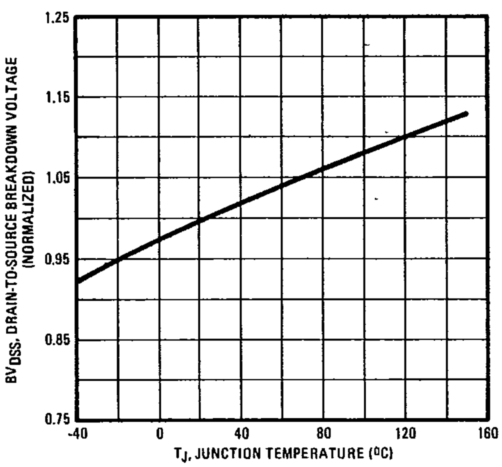

Fig. 8 — Breakdown Voltage Vs. Temperature

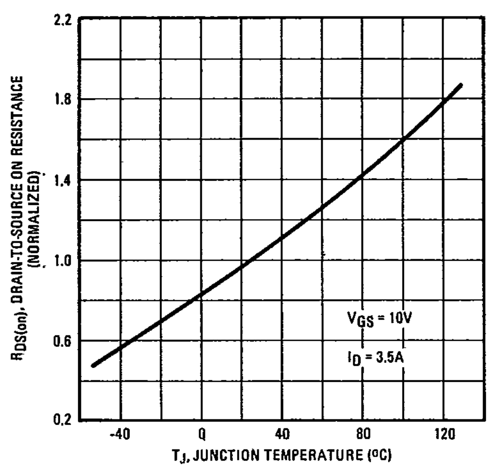

Fig. 9 — Normalized On-Resistance Vs. Temperature

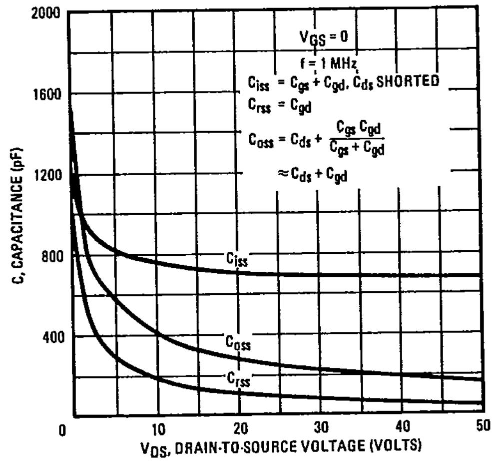

Fig. 10 – Typical Capacitance Vs. Drain-to-Source Voltage

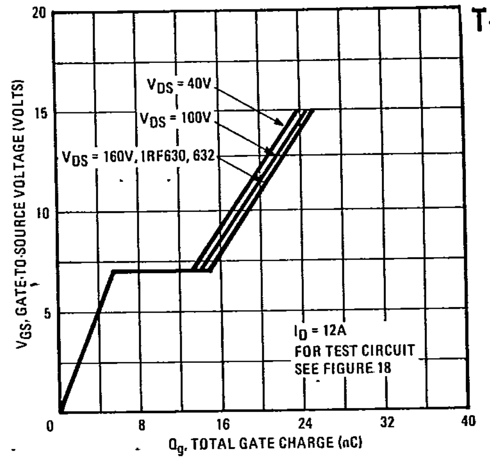

Fig. 11 – Typical Gate Charge Vs. Gate-to-Source Voltage

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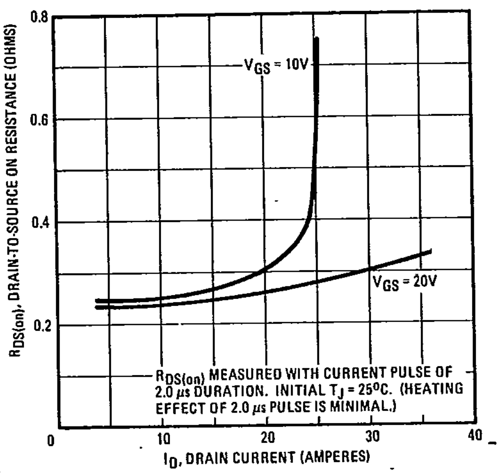

Fig. 12 – Typical On-Resistance Vs. Drain Current

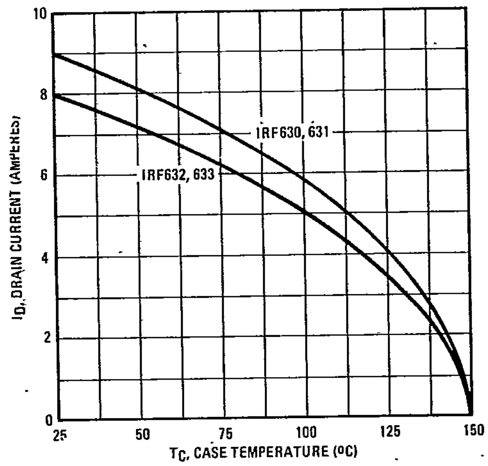

Fig. 13 – Maximum Drain Current Vs. Case Temperature

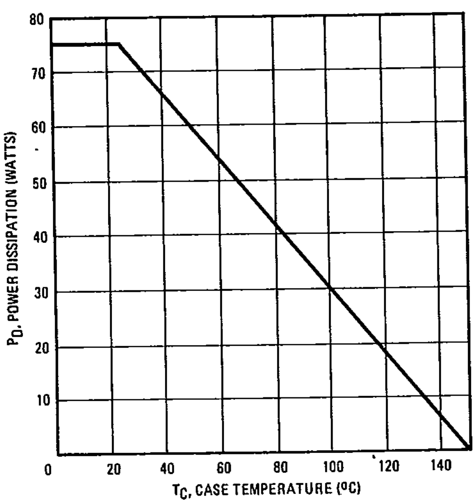

Fig. 14 – Power Vs. Temperature Derating Curve

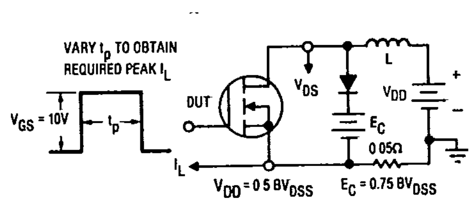

Fig. 15 — Clamped Inductive Test Circuit

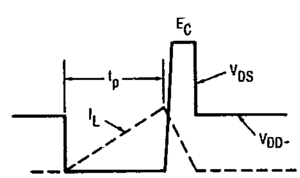

Fig. 16 — Clamped Inductive Waveforms

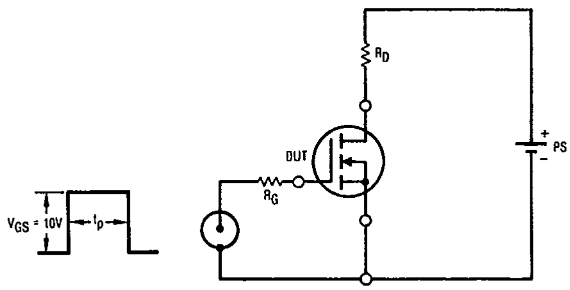

Fig. 17 — Switching Time Test Circuit

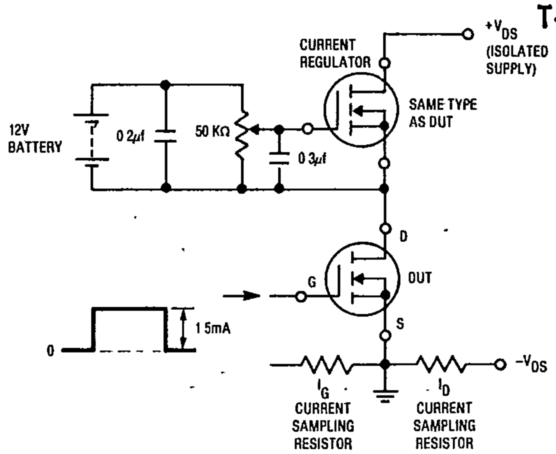

Fig. 18 — Gate Charge Test Circuit

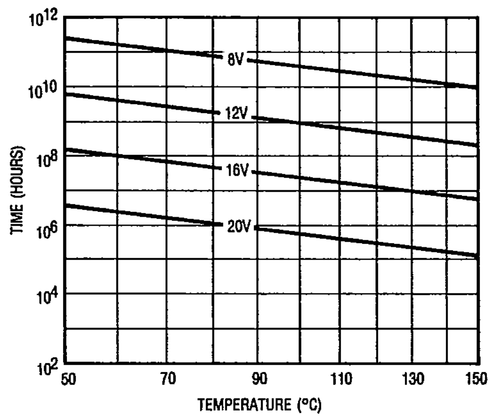

*Fig. 19 — Typical Time to Accumulated 1% Gate Failure

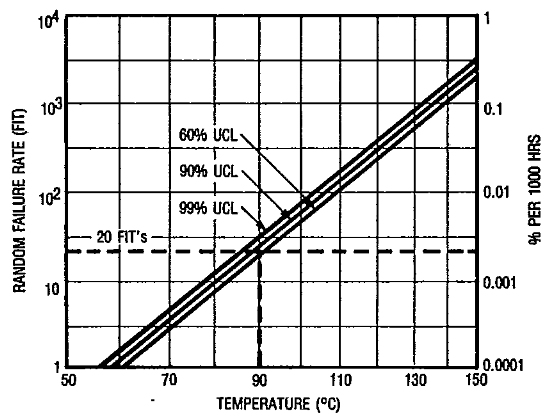

*Fig. 20 — Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1987. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.